



# NX3008CBKV

30 / 30 V, 400 / 220 mA N/P-channel Trench MOSFET

Rev. 1 — 29 July 2011

Product data sheet

## 1. Product profile

### 1.1 General description

Complementary N/P-channel enhancement mode Field-Effect Transistor (FET) in an ultra small and flat lead SOT666 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 1.2 Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 2 kV
- AEC-Q101 qualified

### 1.3 Applications

- Level shifter
- Power supply converter
- Load switch
- Switching circuits

### 1.4 Quick reference data

Table 1. Quick reference data

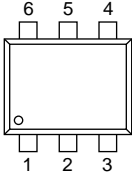
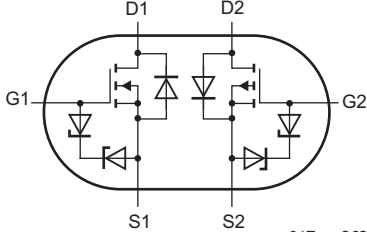
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>TR2 (P-channel)</b>						
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$	-	-	-30	V
$V_{GS}$	gate-source voltage		-8	-	8	V
$I_D$	drain current	$V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ °C}$	[1] -	-	-220	mA
<b>TR1 (N-channel)</b>						
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$	-	-	30	V
$V_{GS}$	gate-source voltage		-8	-	8	V
$I_D$	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ °C}$	[1] -	-	400	mA
<b>TR1 (N-channel), Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 350\text{ mA}; T_j = 25\text{ °C}$	-	1	1.4	$\Omega$
<b>TR2 (P-channel), Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = -4.5\text{ V}; I_D = -200\text{ mA}; T_j = 25\text{ °C}$	-	2.8	4.1	$\Omega$

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	 SOT666 (SOT666)	 017aaa262
2	G1	gate TR1		
3	D2	drain TR2		
4	S2	source TR2		
5	G2	gate TR2		
6	D1	drain TR1		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
NX3008CBKV	SOT666	plastic surface-mounted package; 6 leads	SOT666

4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
NX3008CBKV	AC

[1] % = placeholder for manufacturing site code.

## 5. Limiting values

**Table 5. Limiting values**

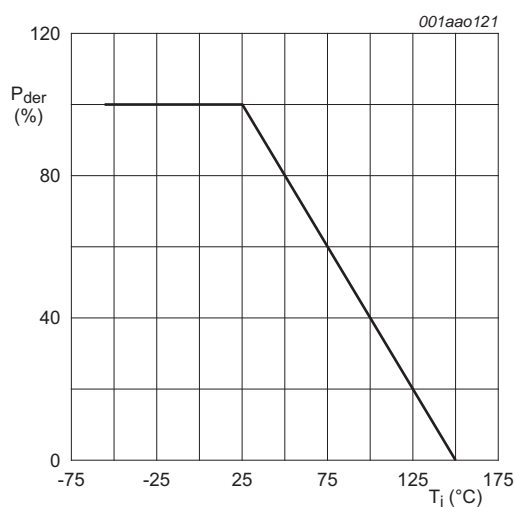
*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit	
TR2 (P-channel)						
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C	-	-30	V	
V <sub>GS</sub>	gate-source voltage		-8	8	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-220	mA
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-140	mA
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs	-	-0.9	A	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	330	mW
			[1]	-	390	mW
		T <sub>sp</sub> = 25 °C	-	-	1090	mW
TR1 (N-channel)						
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C	-	30	V	
V <sub>GS</sub>	gate-source voltage		-8	8	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	400	mA
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	260	mA
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs	-	1.6	A	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	330	mW
			[1]	-	390	mW
		T <sub>sp</sub> = 25 °C	-	-	1090	mW
Per device						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	500	mW
T <sub>j</sub>	junction temperature		-55	150	°C	
T <sub>amb</sub>	ambient temperature		-55	150	°C	
T <sub>stg</sub>	storage temperature		-65	150	°C	
TR1 (N-channel), Source-drain diode						
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	400	mA
TR2 (P-channel), Source-drain diode						
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-220	mA
TR1 N-channel), ESD maximum rating						
V <sub>ESD</sub>	electrostatic discharge voltage	HBM	[3]	-	2000	V
TR2 (P-channel), ESD maximum rating						
V <sub>ESD</sub>	electrostatic discharge voltage	HBM	[3]	-	2000	V

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

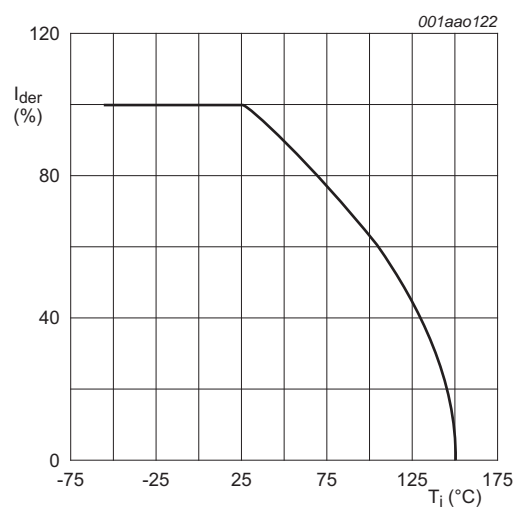
[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard footprint.

[3] Measured between all pins.



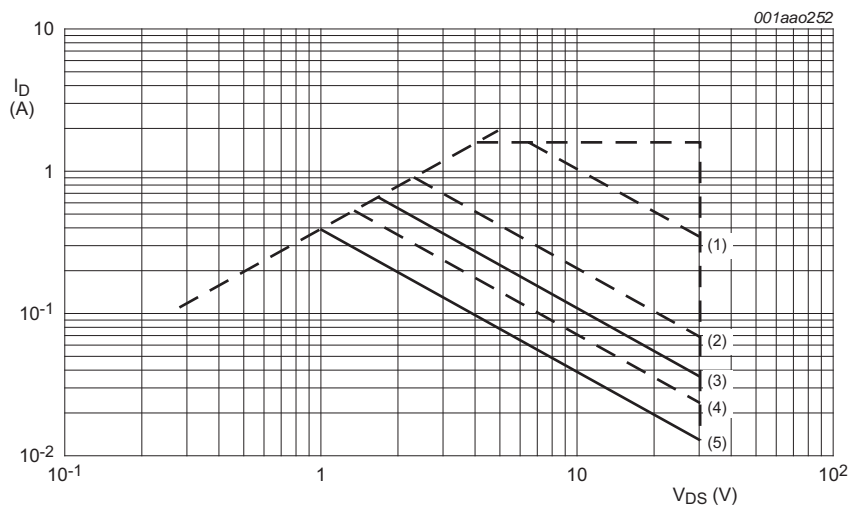
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100\%$$

**Fig 1. Normalized total power dissipation as a function of junction temperature**



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100\%$$

**Fig 2. Normalized continuous drain current as a function of junction temperature**



$I_{DM}$  is a single pulse

(1)  $t_p = 1$  ms

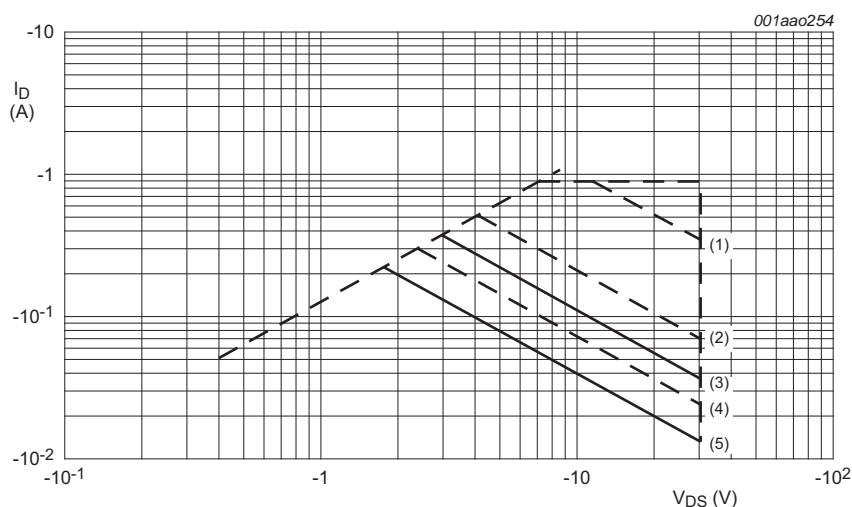
(2)  $t_p = 10$  ms

(3) DC;  $T_{sp} = 25^{\circ}\text{C}$

(4)  $t_p = 100$  ms

(5) DC;  $T_{amb} = 25^{\circ}\text{C}$ ; 1 cm<sup>2</sup> drain mounting pad

**Fig 3. Safe operating area TR1 (N-channel); junction to ambient; continuous and peak drain currents as a function of drain-source voltage**



$I_{DM}$  is a single pulse

(1)  $t_p = 1$  ms

(2)  $t_p = 10$  ms

(3) DC;  $T_{sp} = 25$  °C

(4)  $t_p = 100$  ms

(5) DC;  $T_{amb} = 25$  °C; 1 cm<sup>2</sup> drain mounting pad

**Fig 4.** Safe operating area TR2 (P-channel); junction to ambient; continuous and peak drain currents as a function of drain-source voltage

## 6. Thermal characteristics

**Table 6.** Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per device</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	250 K/W
<b>TR1 (N-channel)</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	330	380 K/W
			[2]	-	280	320 K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	115	K/W
<b>TR2 (P-channel)</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	330	380 K/W
			[2]	-	280	320 K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	115	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

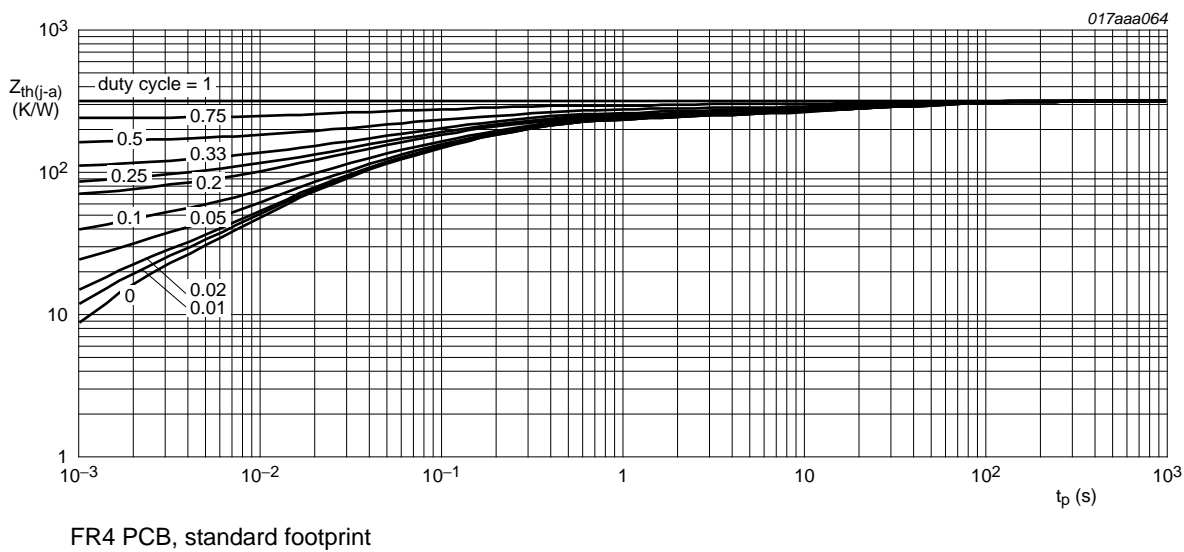


Fig 5. TR1: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

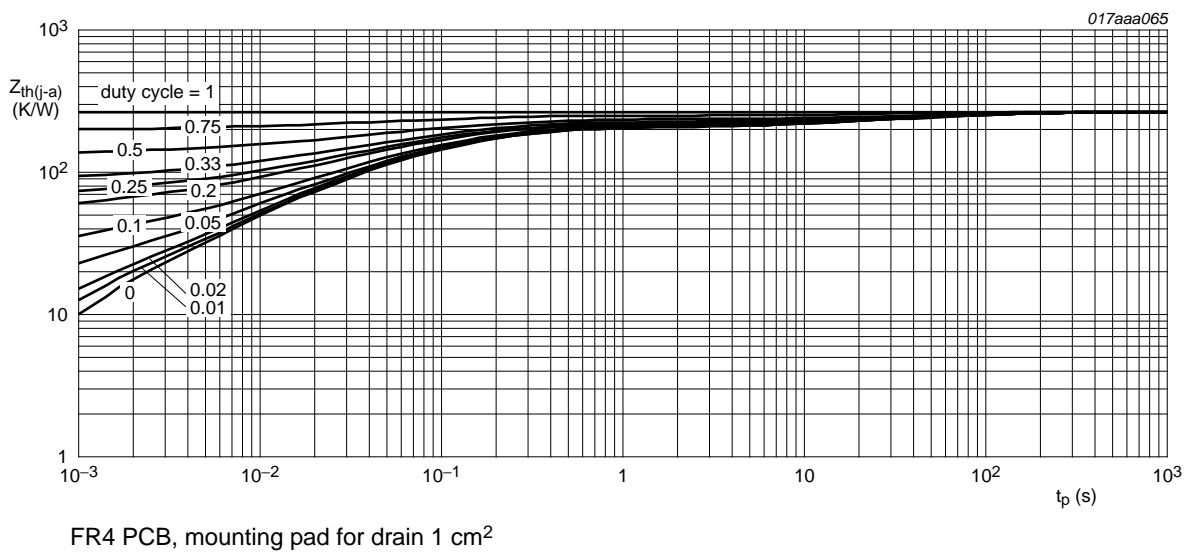
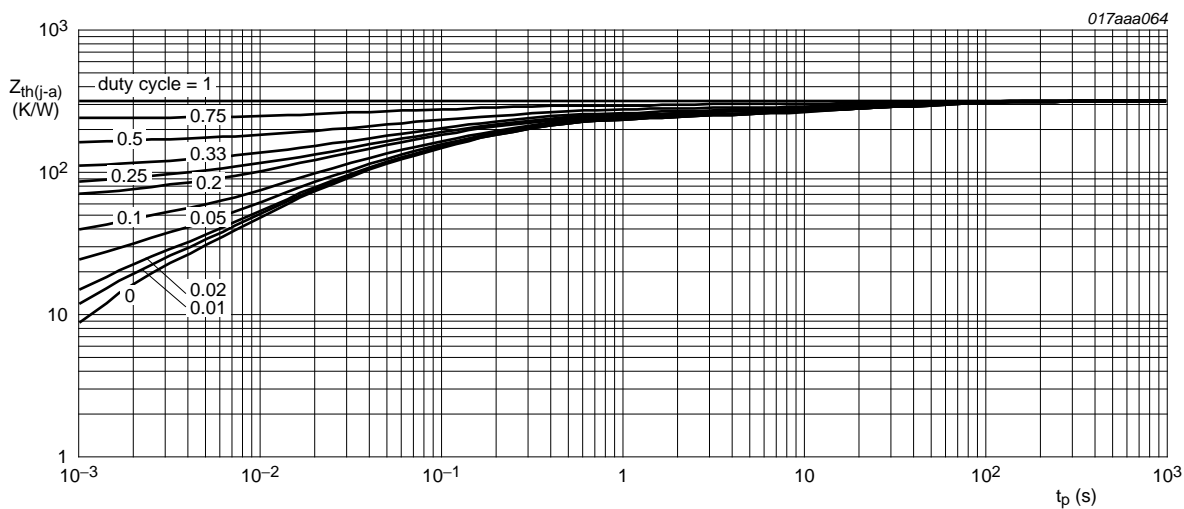
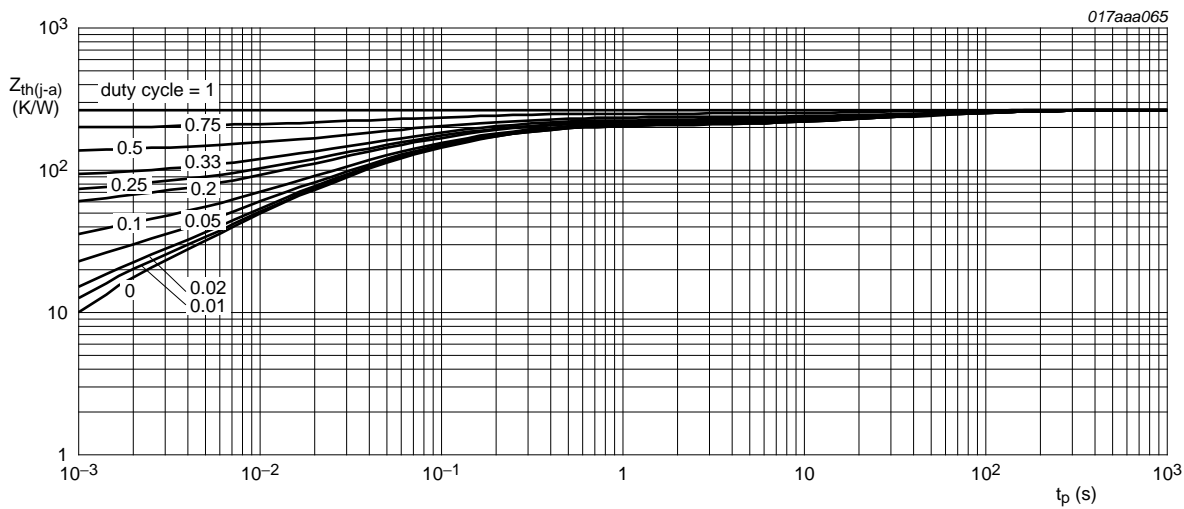


Fig 6. TR1: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, standard footprint

Fig 7. TR2, Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>

Fig 8. TR2, Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>TR2 (P-channel), Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A$ ; $V_{GS} = 0 V$ ; $T_j = 25 ^\circ C$	-30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 ^\circ C$	-0.6	-0.9	-1.1	V
$I_{DSS}$	drain leakage current	$V_{DS} = -30 V$ ; $V_{GS} = 0 V$ ; $T_j = 25 ^\circ C$	-	-	-1	$\mu A$
		$V_{DS} = -30 V$ ; $V_{GS} = 0 V$ ; $T_j = 150 ^\circ C$	-	-	-10	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 8 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 ^\circ C$	-	-0.2	-1	$\mu A$
		$V_{GS} = -8 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 ^\circ C$	-	-0.2	-1	$\mu A$
		$V_{GS} = 4.5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 ^\circ C$	-	-10	-	nA
		$V_{GS} = -4.5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 ^\circ C$	-	-10	-	nA
		$V_{GS} = 2.5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 ^\circ C$	-	-1	-	nA
		$V_{GS} = -2.5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 ^\circ C$	-	-1	-	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = -4.5 V$ ; $I_D = -200 mA$ ; $T_j = 25 ^\circ C$	-	2.8	4.1	$\Omega$
		$V_{GS} = -2.5 V$ ; $I_D = -10 mA$ ; $T_j = 25 ^\circ C$	-	5.3	6.5	$\Omega$
		$V_{GS} = -4.5 V$ ; $I_D = -200 mA$ ; $T_j = 150 ^\circ C$	-	5.3	7.8	$\Omega$
$g_{fs}$	transfer conductance	$V_{DS} = -10 V$ ; $I_D = -200 mA$ ; $T_j = 25 ^\circ C$	-	160	-	mS
<b>TR1 (N-channel), Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A$ ; $V_{GS} = 0 V$ ; $T_j = 25 ^\circ C$	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 ^\circ C$	0.6	0.9	1.1	V
$I_{DSS}$	drain leakage current	$V_{DS} = 30 V$ ; $V_{GS} = 0 V$ ; $T_j = 25 ^\circ C$	-	-	1	$\mu A$
		$V_{DS} = 30 V$ ; $V_{GS} = 0 V$ ; $T_j = 150 ^\circ C$	-	-	10	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 8 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 ^\circ C$	-	0.2	1	$\mu A$
		$V_{GS} = -8 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 ^\circ C$	-	0.2	1	$\mu A$
		$V_{GS} = 4.5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 ^\circ C$	-	10	-	nA
		$V_{GS} = -4.5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 ^\circ C$	-	10	-	nA
		$V_{GS} = 2.5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 ^\circ C$	-	1	-	nA
		$V_{GS} = -2.5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 ^\circ C$	-	1	-	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5 V$ ; $I_D = 350 mA$ ; $T_j = 25 ^\circ C$	-	1	1.4	$\Omega$
		$V_{GS} = 4.5 V$ ; $I_D = 350 mA$ ; $T_j = 150 ^\circ C$	-	1.8	2.5	$\Omega$
		$V_{GS} = 2.5 V$ ; $I_D = 200 mA$ ; $T_j = 150 ^\circ C$	-	1.4	2.1	$\Omega$
		$V_{GS} = 1.8 V$ ; $I_D = 10 mA$ ; $T_j = 25 ^\circ C$	-	2	2.8	$\Omega$
$g_{fs}$	transfer conductance	$V_{DS} = 10 V$ ; $I_D = 350 mA$ ; $T_j = 25 ^\circ C$	-	310	-	mS
<b>TR1 (N-channel), Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 15 V$ ; $I_D = 400 mA$ ; $V_{GS} = 4.5 V$ ; $T_j = 25 ^\circ C$	-	0.52	0.68	nC
$Q_{GS}$	gate-source charge		-	0.17	-	nC
$Q_{GD}$	gate-drain charge		-	0.08	-	nC



Table 7. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$C_{iss}$	input capacitance	$V_{DS} = 15\text{ V}; f = 1\text{ MHz}; V_{GS} = 0\text{ V};$ $T_j = 25\text{ }^{\circ}\text{C}$	-	34	50	pF
$C_{oss}$	output capacitance		-	6.5	-	pF
$C_{rss}$	reverse transfer capacitance		-	2.2	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 20\text{ V}; R_L = 250\text{ }\Omega; V_{GS} = 4.5\text{ V};$ $R_{G(ext)} = 6\text{ }\Omega; T_j = 25\text{ }^{\circ}\text{C}$	-	15	30	ns
$t_r$	rise time		-	11	-	ns
$t_{d(off)}$	turn-off delay time		-	69	138	ns
$t_f$	fall time		-	19	-	ns
<b>TR2 (P-channel), Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = -15\text{ V}; I_D = -200\text{ mA};$ $V_{GS} = -4.5\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$	-	0.55	0.72	nC
$Q_{GS}$	gate-source charge		-	0.23	-	nC
$Q_{GD}$	gate-drain charge		-	0.09	-	nC
$C_{iss}$	input capacitance	$V_{DS} = -15\text{ V}; f = 1\text{ MHz}; V_{GS} = 0\text{ V};$ $T_j = 25\text{ }^{\circ}\text{C}$	-	31	46	pF
$C_{oss}$	output capacitance		-	6.5	-	pF
$C_{rss}$	reverse transfer capacitance		-	2.3	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = -20\text{ V}; R_L = 250\text{ }\Omega; V_{GS} = -4.5\text{ V};$ $R_{G(ext)} = 6\text{ }\Omega; T_j = 25\text{ }^{\circ}\text{C}$	-	19	38	ns
$t_r$	rise time		-	30	-	ns
$t_{d(off)}$	turn-off delay time		-	65	130	ns
$t_f$	fall time		-	38	-	ns
<b>TR2 (P-channel), Source-drain diode characteristics</b>						
$V_{SD}$	source-drain voltage	$I_S = -200\text{ mA}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$	-0.47	-0.88	-1.2	V
<b>TR1 (N-channel), Source-drain diode characteristics</b>						
$V_{SD}$	source-drain voltage	$I_S = 350\text{ mA}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$	0.47	0.85	1.2	V

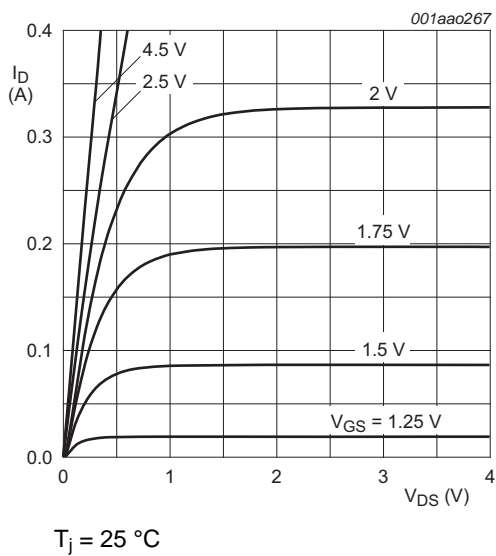


Fig 9. TR1: Output characteristics: drain current as a function of drain-source voltage; typical values

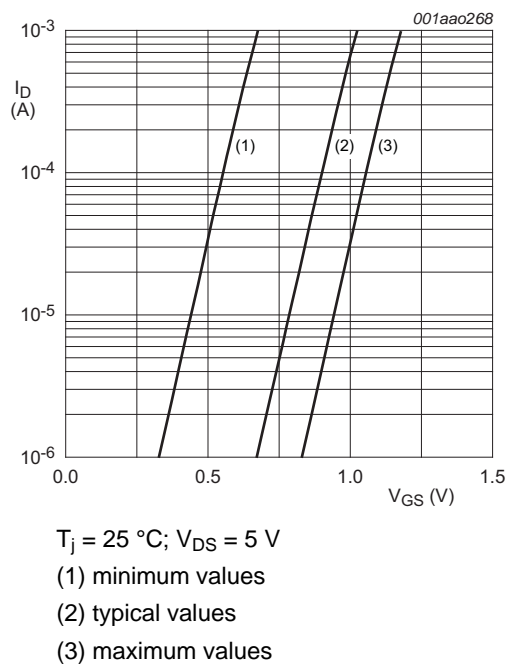


Fig 10. TR1: Sub-threshold drain current as a function of gate-source voltage

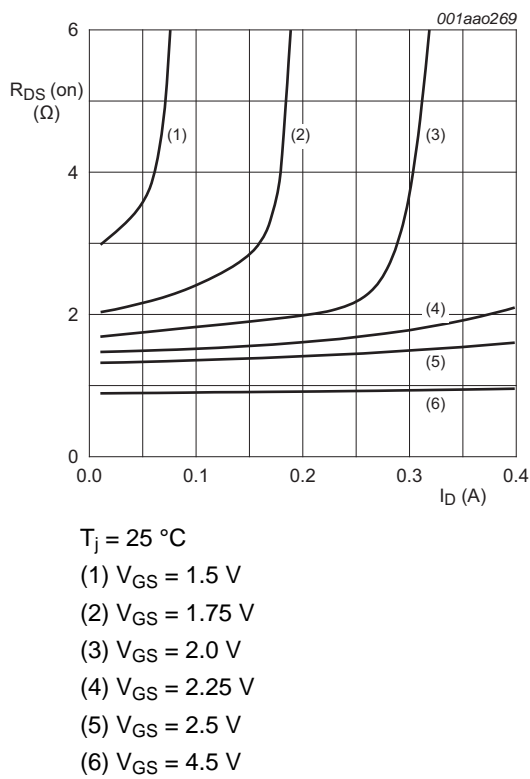


Fig 11. TR1: Drain-source on-state resistance as a function of drain current; typical values

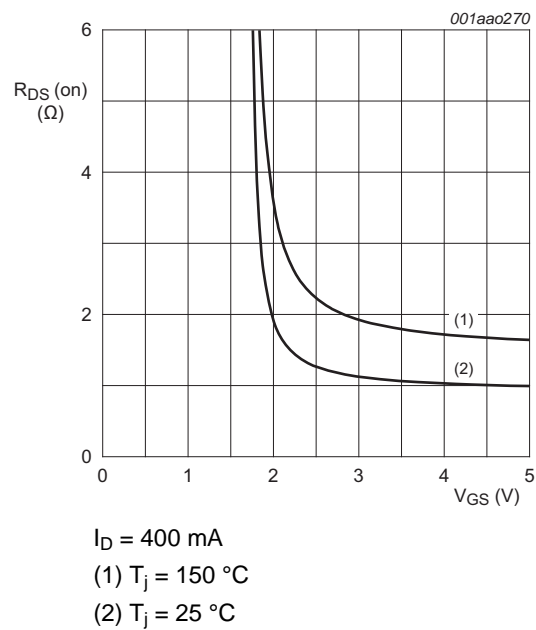
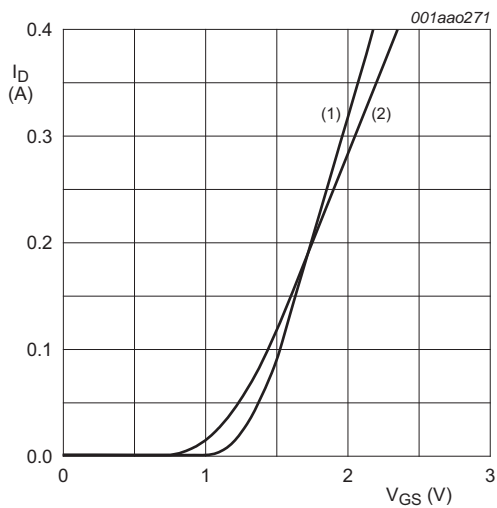
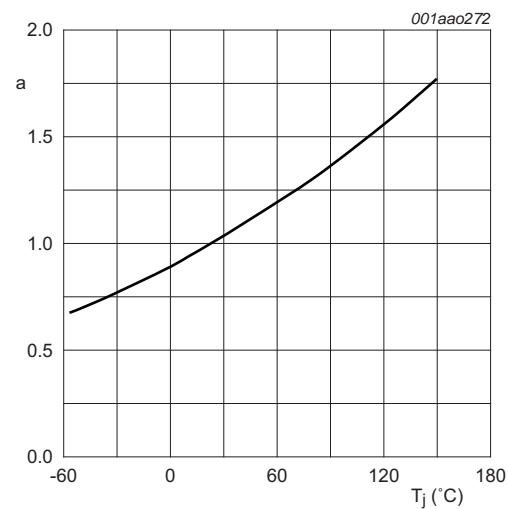


Fig 12. TR1: Drain-source on-state resistance as a function of gate-source voltage; typical values



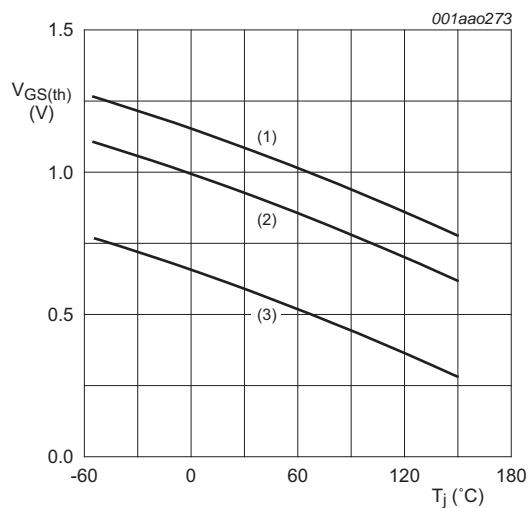
$V_{DS} > I_D \times R_{DSon}$   
(1)  $T_j = 25\text{ }^{\circ}\text{C}$   
(2)  $T_j = 150\text{ }^{\circ}\text{C}$

Fig 13. TR1: Transfer characteristics: drain current as a function of gate-source voltage; typical values



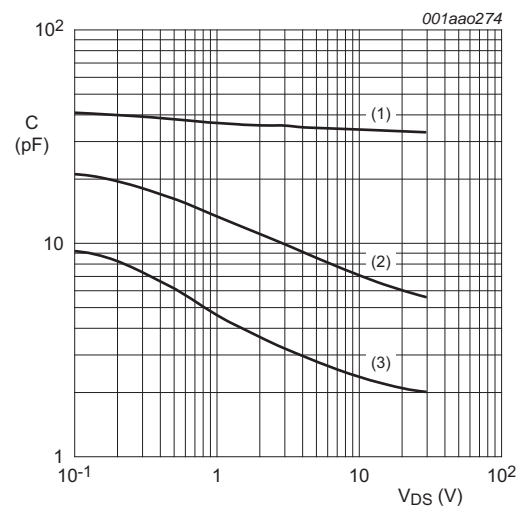
$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}\text{C})}$$

Fig 14. TR1: Normalized drain-source on-state resistance as a function of junction temperature; typical values



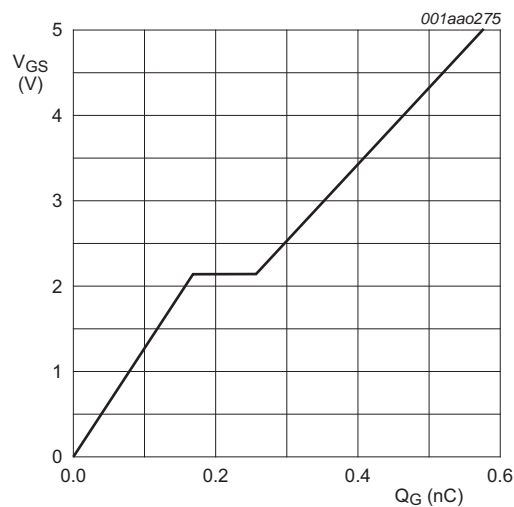
$I_D = 0.25\text{ mA}; V_{DS} = V_{GS}$   
(1) maximum values  
(2) typical values  
(3) minimum values

Fig 15. TR1: Gate-source threshold voltage as a function of junction temperature



$f = 1\text{ MHz}; V_{GS} = 0\text{ V}$   
(1)  $C_{iss}$   
(2)  $C_{oss}$   
(3)  $C_{rss}$

Fig 16. TR1: Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$I_D = 0.4 \text{ A}$ ;  $V_{DS} = 15 \text{ V}$ ;  $T_{amb} = 25 \text{ }^{\circ}\text{C}$

Fig 17. TR1: Gate-source voltage as a function of gate charge; typical values

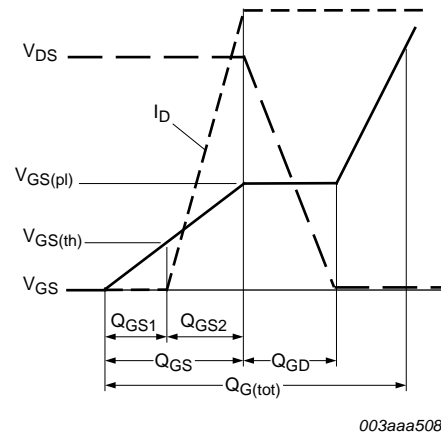
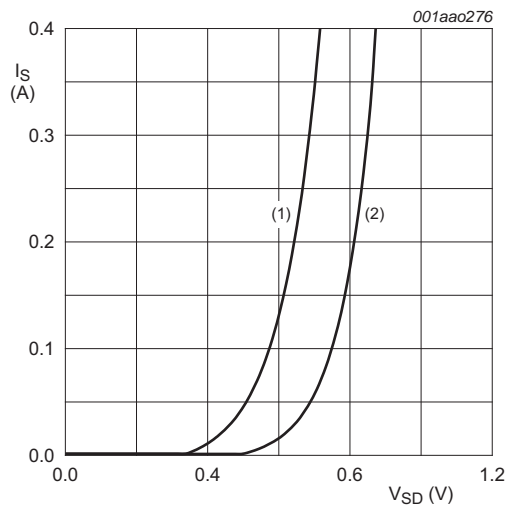
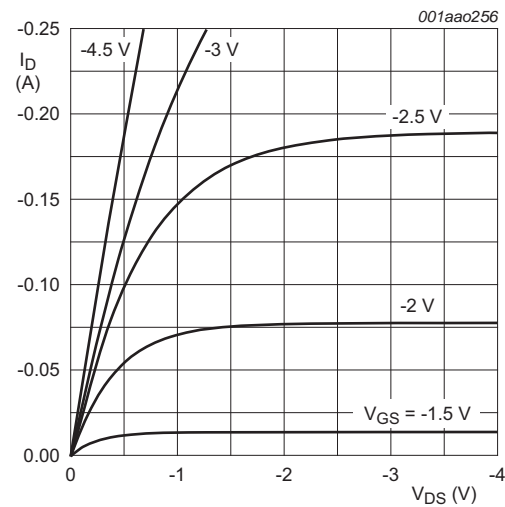


Fig 18. Gate charge waveform definitions



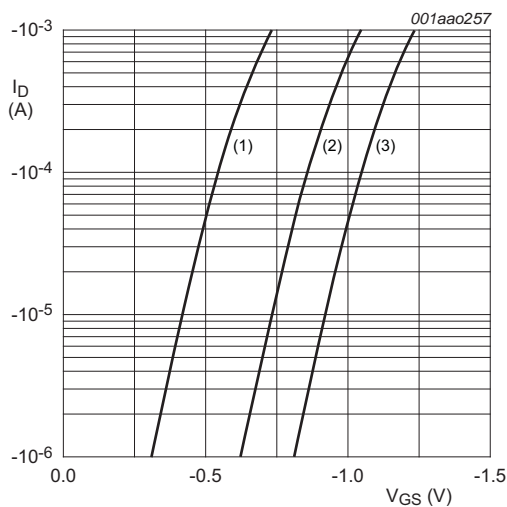
$V_{GS} = 0 \text{ V}$   
(1)  $T_j = 150 \text{ }^{\circ}\text{C}$   
(2)  $T_j = 25 \text{ }^{\circ}\text{C}$

Fig 19. TR1: Source current as a function of source-drain voltage; typical values



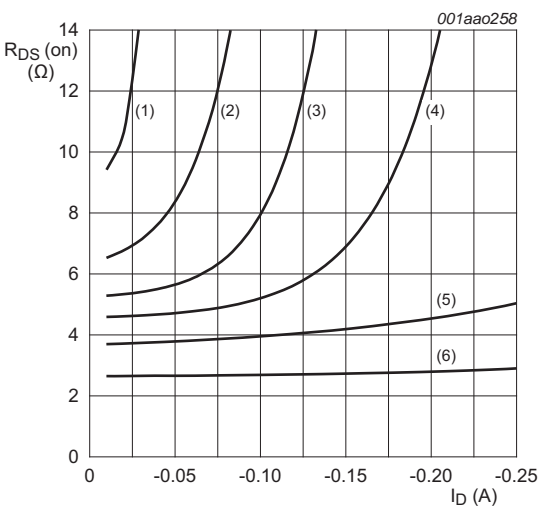
$T_j = 25 \text{ }^{\circ}\text{C}$

Fig 20. TR2: Output characteristics: drain current as a function of drain-source voltage; typical values



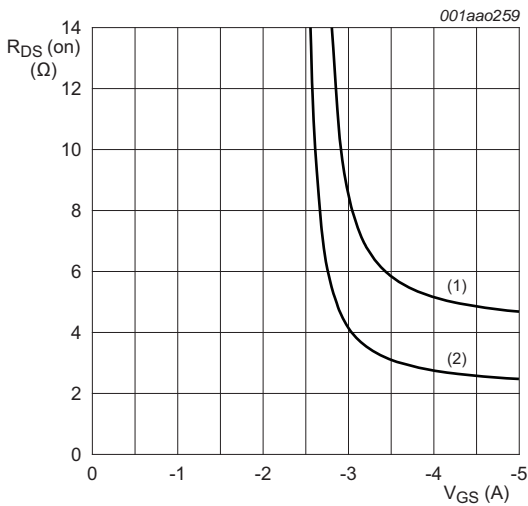
$T_j = 25\text{ }^{\circ}\text{C}$ ;  $V_{DS} = -5\text{ V}$   
(1) minimum values  
(2) typical values  
(3) maximum values

Fig 21. TR2: Sub-threshold drain current as a function of gate-source voltage



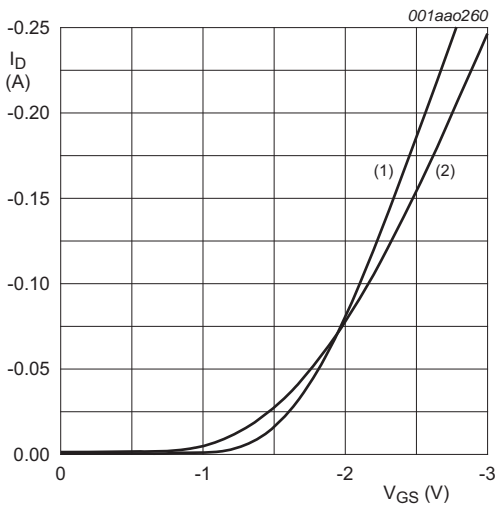
$T_j = 25\text{ }^{\circ}\text{C}$   
(1)  $V_{GS} = -1.75\text{ V}$   
(2)  $V_{GS} = -2.0\text{ V}$   
(3)  $V_{GS} = -2.25\text{ V}$   
(4)  $V_{GS} = -2.5\text{ V}$   
(5)  $V_{GS} = -3.0\text{ V}$   
(6)  $V_{GS} = -4.5\text{ V}$

Fig 22. TR2: Drain-source on-state resistance as a function of drain current; typical values



$I_D = -200\text{ mA}$   
(1)  $T_j = 150\text{ }^{\circ}\text{C}$   
(2)  $T_j = 25\text{ }^{\circ}\text{C}$

Fig 23. TR2: Drain-source on-state resistance as a function of gate-source voltage; typical values



$V_{DS} > I_D \times R_{DS(on)}$   
(1)  $T_j = 25\text{ }^{\circ}\text{C}$   
(2)  $T_j = 150\text{ }^{\circ}\text{C}$

Fig 24. TR2: Transfer characteristics: drain current as a function of gate-source voltage; typical values

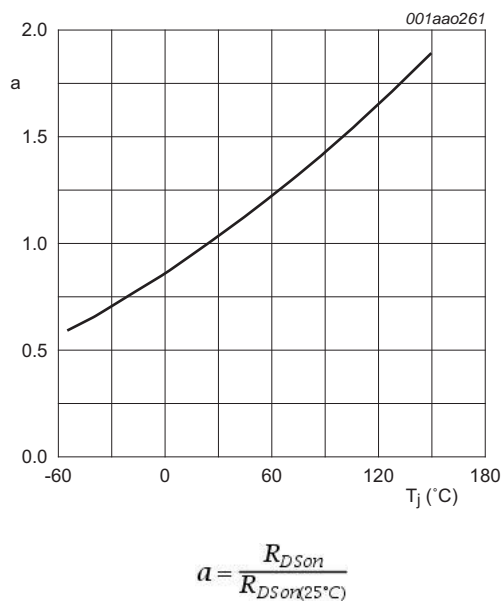


Fig 25. TR2: Normalized drain-source on-state resistance as a function of junction temperature; typical values

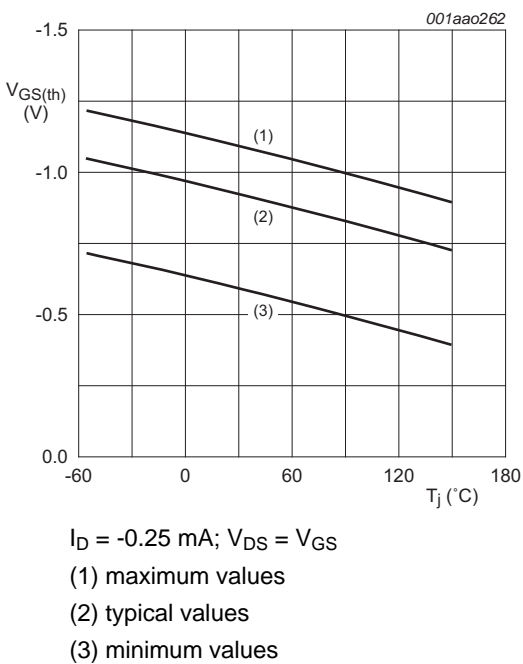


Fig 26. TR2: Gate-source threshold voltage as a function of junction temperature

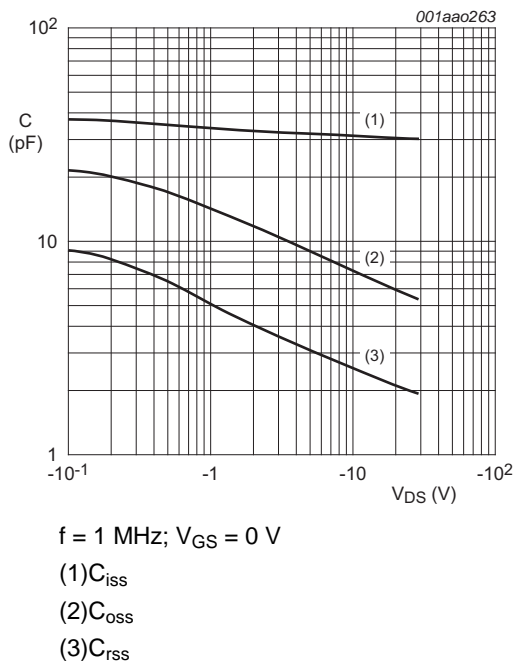


Fig 27. TR2: Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

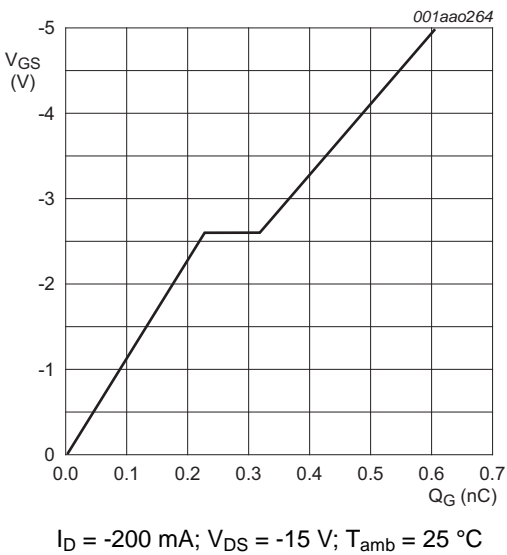


Fig 28. Gate-source voltage as a function of gate charge; typical values

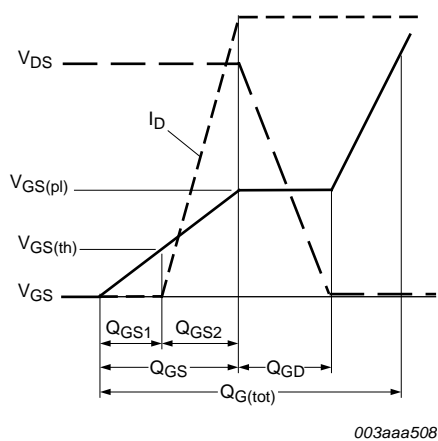


Fig 29. Gate charge waveform definitions

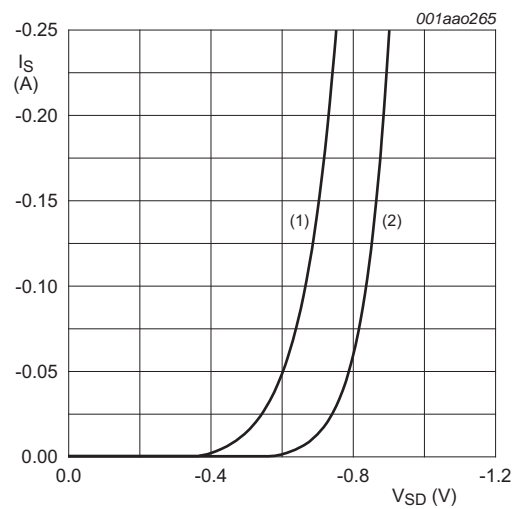


Fig 30. TR2: Source current as a function of source-drain voltage; typical values

8. Test information

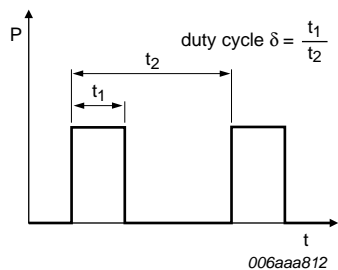


Fig 31. Duty cycle definition

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline

Plastic surface-mounted package; 6 leadsSOT666

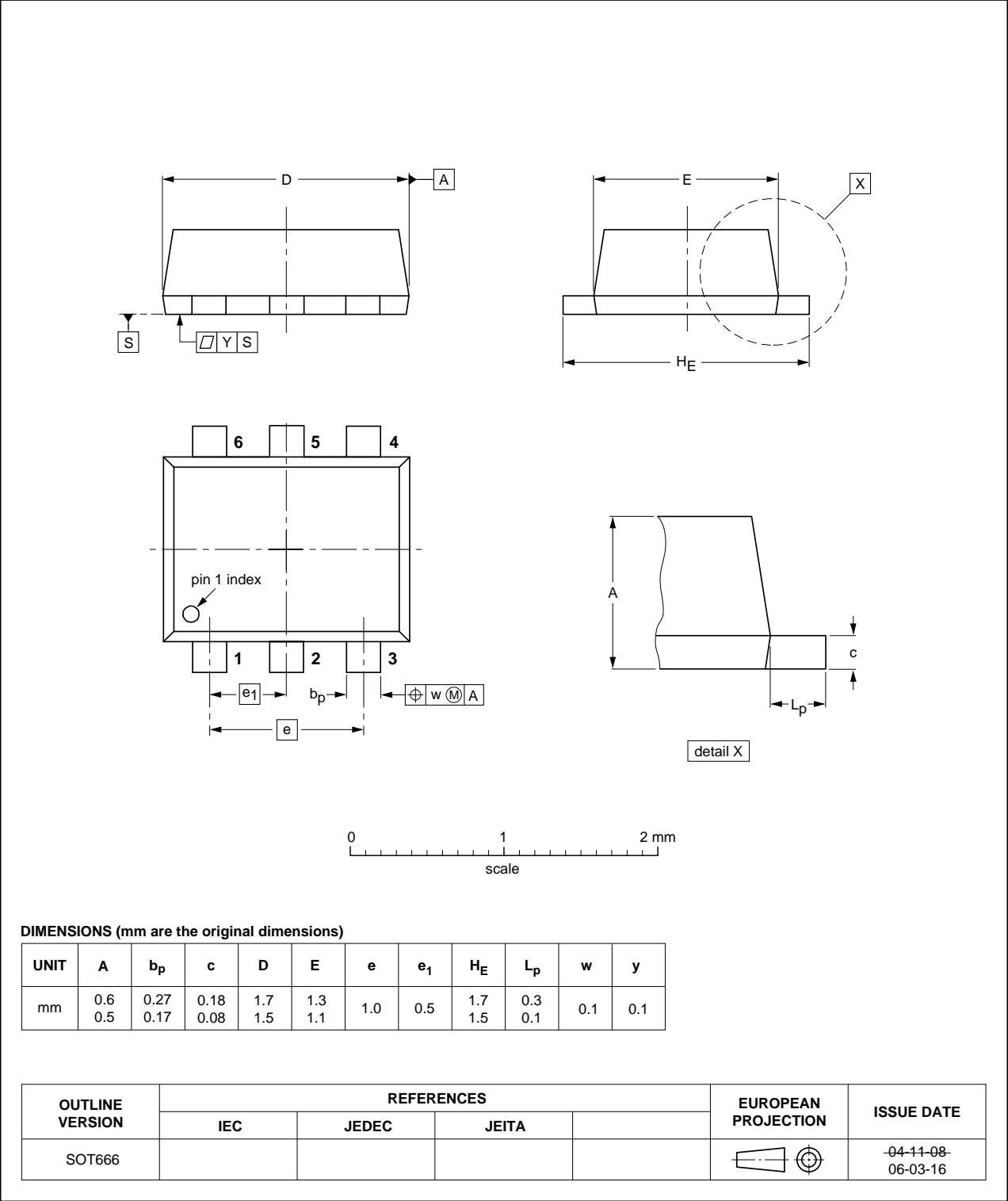


Fig 32. Package outline SOT666 (SOT666)



10. Soldering

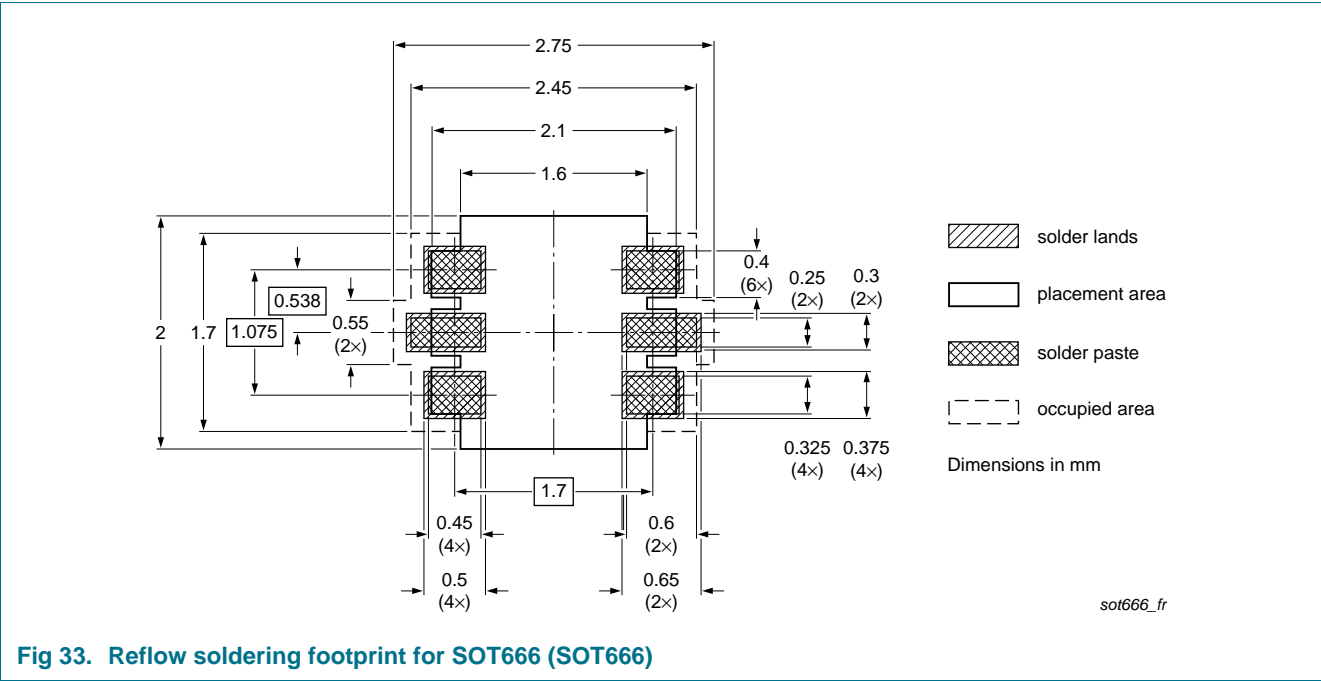


Fig 33. Reflow soldering footprint for SOT666 (SOT666)

## 11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NX3008CBKV v.1	20110729	Product data sheet	-	-

## 12. Legal information

### 12.1 Data sheet status

Document status <sup>[1] [2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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